/ Descriptions

TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

/ Features

$V_{CE(sat)}$,h_{FE}

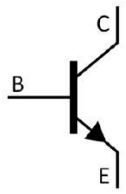
Low saturation voltage, excellent h_{FE} linearity and high h_{FE}.

/ Applications

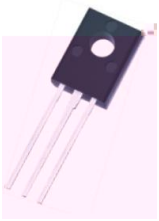
3 , ,

Output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

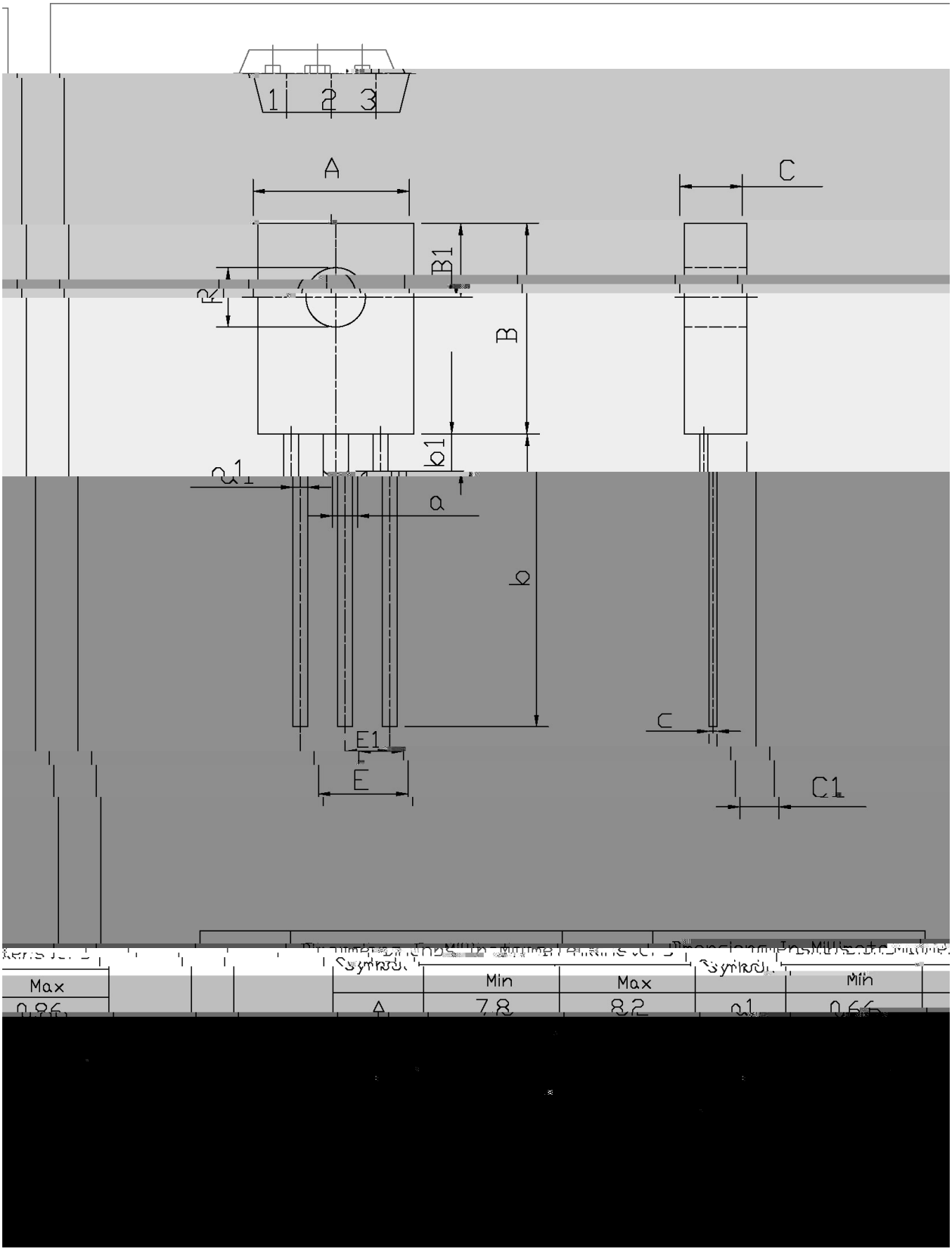
h_{FE} Classifications	R	Q	P	E
Symbol				

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation	P_C	1.0	W
	$P_C(T_C=25\ \ )$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=3.0V I_C=0			1.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=1.0A	60	160	400	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=20mA	30	150		

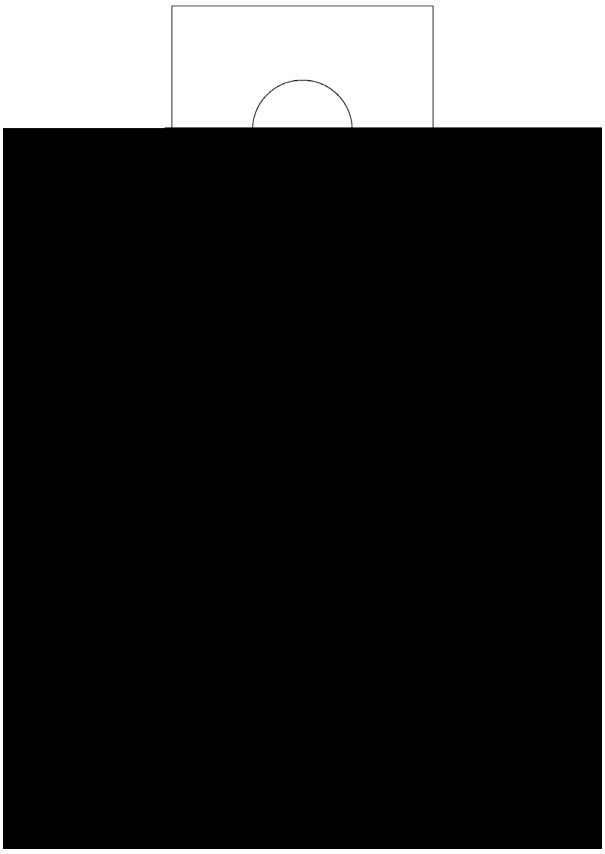
/ Package Dimensions

TO-126T 单位：mm



Max	Symbol	Min	Max	Symbol	Min
0.86	A	7.8	8.2	a1	0.66

/ Marking Instructions



BR

D882

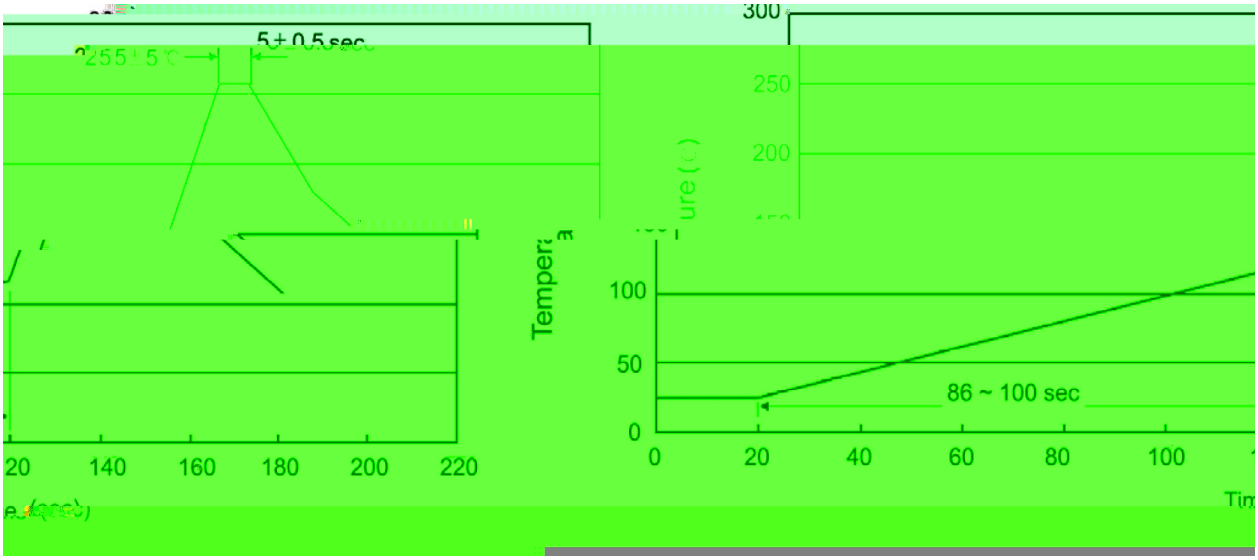
R: h_{FE}

****

Note:

BR:	Company Code
D882:	Product Type Code.
R:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

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